

[MASK ROM STRUCTURE AND MANUFACTURING METHOD THEREOF]

Abstract

A mask read-only-memory structure and its method of manufacture are provided. The structure includes a substrate, a buried bit line in the substrate and a patterned stack layer covering a portion of the upper surface of the substrate. The stack layer includes a first dielectric layer, a stopping layer and a second dielectric layer. A gate oxide layer covers a portion of the upper surface of the substrate. A word line runs across the buried bit line to form a plurality of coding cells. The memory cells having a stack layer thereon are at a logic state "0" while the memory cells having a gate oxide layer thereon are at a logic state "1".